



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s) : James S. Im Customer No. : 21003
Serial No. : 10/525,288 Confirmation No. : 7758
Filed : 02/16/2005 Group Art Unit : 2813
Examiner :
For : Process And System For Laser Crystallization Processing Of Film Regions
On A Substrate To Provide Substantial Uniformity, And A Structure Of
Such Film Regions

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

I hereby certify that this paper is being deposited with the United States
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David Schalk
Name of Person
Certifying

David Schalk
Signature

March 27, 2006
Date of Signature

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

Pursuant to 37 C.F.R. §§ 1.56 and 1.97(b), applicants bring to the attention of
the Examiner the document listed on the attached Form PTO-1449 and respectfully request
that the listed documents be considered by the Examiner and made of record in the above-
captioned application. Copies of all U.S. Patents and Applications are not enclosed pursuant

to the waiver of 37 CFR 1.98 (a)(2)(i) for all applications filed after June 30, 2003.
03/30/2006 WABDEL1 0000045 024377 10525288

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This submission does not represent that a search has been made or that no better art exists and does not constitute an admission that the listed documents are material or constitute "prior art." If the Examiner applies the documents as prior art against any claim in the application and applicants determine that the cited documents do not constitute "prior art" under United States law, applicants reserve the right to present to the Office the relevant facts and law regarding the appropriate status of the documents.

Applicants further reserve the right to take appropriate action to establish the patentability of the disclosed invention over the listed documents, should the documents be applied against the claims of the present application.

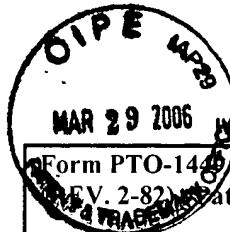
Applicants have enclosed the required fee of \$180.00 due in connection with this. If any additional fee is due, or if any overpayment has been made, the Commissioner is authorized to charge any such fee or credit any overpayment, to our Deposit Account No. 02-4377.

Respectfully submitted,

BAKER BOTTS L.L.P.

By:


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212-408-2500



Form PTO-144 U.S. Department of Commerce
REV. 2-82 Patent and Trademark Office

**INFORMATION DISCLOSURE STATEMENT
BY APPLICANT**

(Use several sheets if necessary)

Atty. Docket No. A35760-PCT-USA (070050.2713)	Serial No. 10/525,288
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Applicant James S. Im

Filing Date 02/16/2005	Group 2813
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Examiner

U.S. PATENT DOCUMENTS

Exam. Initial.	No.	Document No.	Issue/Publication Date	Applicant(s)
	1.	3632205	01/04/1972	Marcy
	2.	4234358	11/18/1980	Celler et al.
	3.	4309225	01/05/1982	Fan et al.
	4.	4382658	05/10/1983	Shields et al.
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	6.	4639277	01/27/1987	Hawkins
	7.	4691983	09/08/1987	Kobayashi et al.
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	10.	4793694	12/27/1988	Liu
	11.	4800179	01/1989	Mukai
	12.	4855014	08/1989	Kakimoto et al.
	13.	4870031	09/1989	Suguhara et al.
	14.	4940505	07/1990	Schachameyer et al.
	15.	4970546	11/1990	Suzuki et al.

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Date Considered

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Exam. Initial.	No.	Document No.	Issue/Publication Date	Applicant(s)
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Exam. Initial.	No.	Document No.	Issue/Publication Date	Applicant(s)
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	52.	6172820	01/2001	Kuwahara.
	53.	6177301	01/2001	Jung
	54.	6187088	02/01/2001	Okumura
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Exam Initial	No.	Document No.	Publication Date	Country	Translation Yes No
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	99.	1067593	10/01/2001	EP	
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	104.	2283036	11/20/1990	JP	<u>No</u>
	105.	6252048	09/09/1994	JP	<u>No</u>
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	107.	7176757	07/14/1995	JP	<u>No</u>
	108.	11064883	03/05/1999	JP	<u>No</u>
	109.	04033327		JP	<u>No</u>
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	111.	62181419	08/08/1987	JP	
	112.	9824118	06/04/1998	WO	

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Exam Initial	No.	Document No.	Publication Date	Country	Translation Yes No
	113.	9931719	06/24/1999	WO	<u>No</u>
	114.	0014784	03/16/2000	WO	
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Exam Initial	No.	Document No.	Publication Date	Country	Translation	
					Yes	No
	129.	04017380	02/26/2004	WO		
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Exam Initial	No.	OTHER DOCUMENTS (including Author, Title, Date, Pertinent Pages, Etc.)	
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	132.	S.D. Brotherton et al., "Influence of Melt Depth in Laser Crystallized Poly-Si Thin Film Transistors," 82 J. Appl. Phys. 4086 (1997).	
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	137.	Sposili et al., "Single-Crystal Si Films via a Low-Substrate-Temperature Excimer-Laser Crystallization Method", Mat. Res. Soc. Symp. Proc. vol. 452, pp. 953-958, 1997 Materials Research Society.*	
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	156.	Yoshimoto, et al., "Excimer-Laser-Produced and Two-Dimensionally Position-Controlled Giant Si Grains on Organic SOG Underlayer", p. 285-286, AM-LCD 2000. No month.	
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